

# FGPF15N60UNDF

## 600 V, 15 A Short Circuit Rated IGBT

### Features

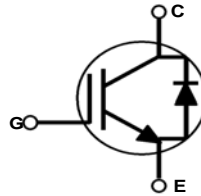
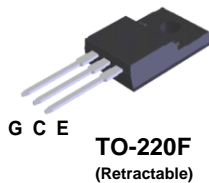
- Short Circuit Rated 10us
- High Current Capability
- High Input Impedance
- Fast Switching
- RoHS Compliant

### General Description

Using advanced NPT IGBT technology, Fairchild's the NPT IGBTs offer the optimum performance for low-power inverter-driven applications where low-losses and short-circuit ruggedness features are essential, such as sewing machine, CNC, motor control and home appliances.

### Applications

- Sewing Machine, CNC, Home Appliances, Motor Control



### Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
$V_{CES}$	Collector to Emitter Voltage	600	V
$V_{GES}$	Gate to Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C = 25^\circ\text{C}$	30	A
	Collector Current @ $T_C = 100^\circ\text{C}$	15	A
$I_{CM(1)}$	Pulsed Collector Current @ $T_C = 25^\circ\text{C}$	45	A
$I_F$	Diode Forward Current @ $T_C = 25^\circ\text{C}$	15	A
	Diode Forward Current @ $T_C = 100^\circ\text{C}$	7.5	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	42	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	17	W
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$

**Notes:**

1: Repetitive rating: Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	3.0	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case	-	4.9	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (PCB Mount)(2)	-	62.5	$^\circ\text{C}/\text{W}$

**Notes:**

2: Mounted on 1" square PCB (FR4 or G-10 material)

**Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGPF15N60UNDF	FGPF15N60UNDF	TO-220F	-	-	50ea

**Electrical Characteristics of the IGBT**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$BV_{CES}$	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	600	-	-	V
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	1	mA
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	$\pm 10$	$\mu\text{A}$
<b>On Characteristics</b>						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 15\text{ mA}, V_{CE} = V_{GE}$	5.5	6.8	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 15\text{ A}, V_{GE} = 15\text{ V}$	-	2.2	2.7	V
		$I_C = 15\text{ A}, V_{GE} = 15\text{ V}, T_C = 125^\circ\text{C}$	-	2.7	-	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	619	-	pF
$C_{oes}$	Output Capacitance		-	80	-	pF
$C_{res}$	Reverse Transfer Capacitance		-	24	-	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 15\text{ A}, R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	-	9.3	-	ns
$t_r$	Rise Time		-	9.8	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	54.8	-	ns
$t_f$	Fall Time		-	9.9	12.8	ns
$E_{on}$	Turn-On Switching Loss		-	0.37	-	mJ
$E_{off}$	Turn-Off Switching Loss		-	0.067	-	mJ
$E_{ts}$	Total Switching Loss		-	0.44	-	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 15\text{ A}, R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 125^\circ\text{C}$	-	8.9	-	ns
$t_r$	Rise Time		-	9.9	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	56.6	-	ns
$t_f$	Fall Time		-	13.2	-	ns
$E_{on}$	Turn-On Switching Loss		-	0.54	-	mJ
$E_{off}$	Turn-Off Switching Loss		-	0.11	-	mJ
$E_{ts}$	Total Switching Loss		-	0.65	-	mJ
$T_{sc}$	Short Circuit Withstand Time	$V_{CC} = 350\text{ V}, R_G = 100\ \Omega, V_{GE} = 15\text{ V}, T_C = 150^\circ\text{C}$	10	-	-	$\mu\text{s}$

**Electrical Characteristics of the IGBT**  $T_C = 25^\circ\text{C}$  unless otherwise noted

$Q_g$	Total Gate Charge	$V_{CE} = 400\text{ V}, I_C = 15\text{ A},$ $V_{GE} = 15\text{ V}$	-	43	-	nC
$Q_{ge}$	Gate to Emitter Charge		-	6	-	nC
$Q_{gc}$	Gate to Collector Charge		-	26	-	nC

**Electrical Characteristics of the Diode**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit	
$V_{FM}$	Diode Forward Voltage	$I_F = 15\text{ A}$	$T_C = 25^\circ\text{C}$	-	1.6	2.2	V
			$T_C = 125^\circ\text{C}$	-	1.5	-	
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 15\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	82.4	-	ns
			$T_C = 125^\circ\text{C}$	-	142	-	
$Q_{rr}$	Diode Reverse Recovery Charge	$I_F = 15\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	213	-	nC
			$T_C = 125^\circ\text{C}$	-	541	-	

## Typical Performance Characteristics

Figure 1. Typical Output Characteristics

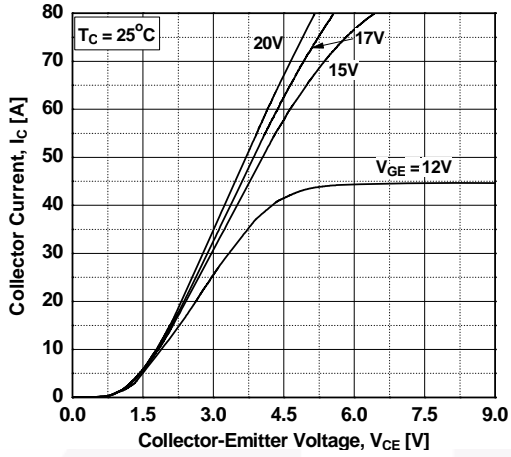


Figure 2. Typical Output Characteristics

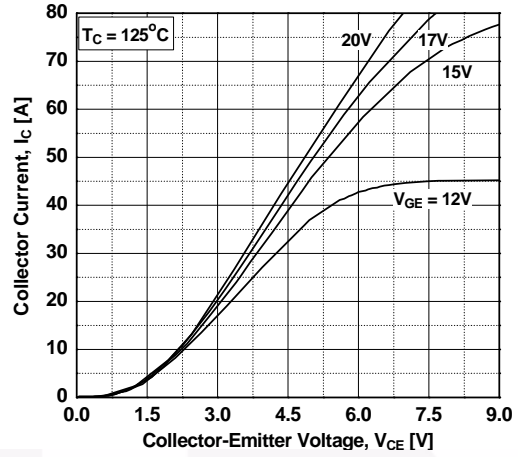


Figure 3. Typical Saturation Voltage Characteristics

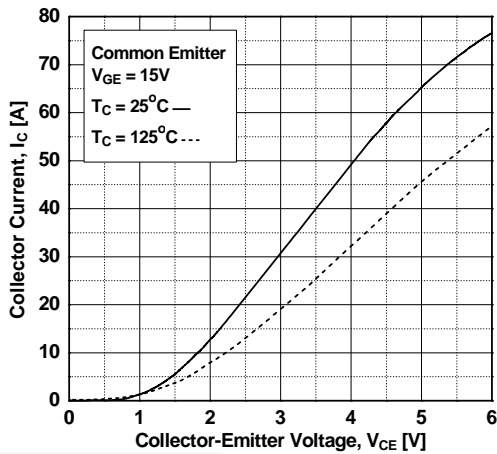


Figure 4. Transfer Characteristics

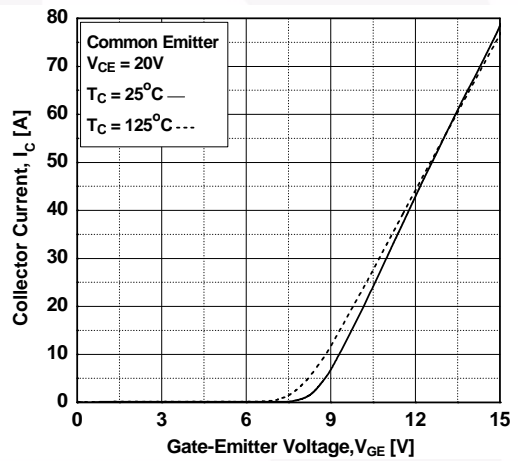


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

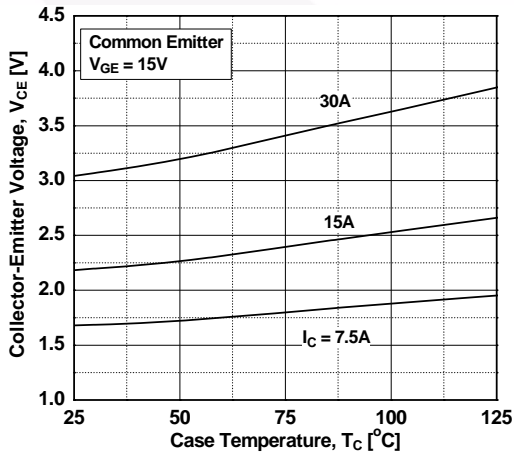
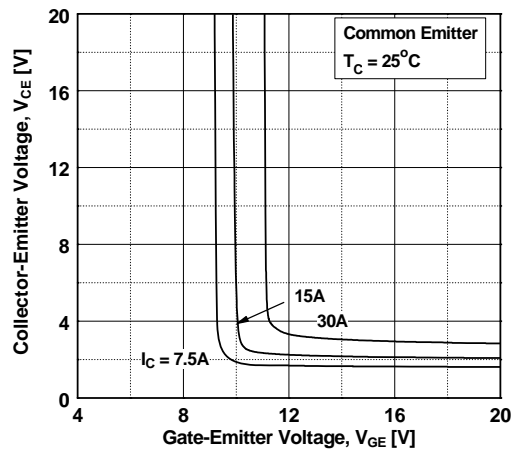


Figure 6. Saturation Voltage vs. Vge



## Typical Performance Characteristics

Figure 7. Saturation Voltage vs.  $V_{GE}$

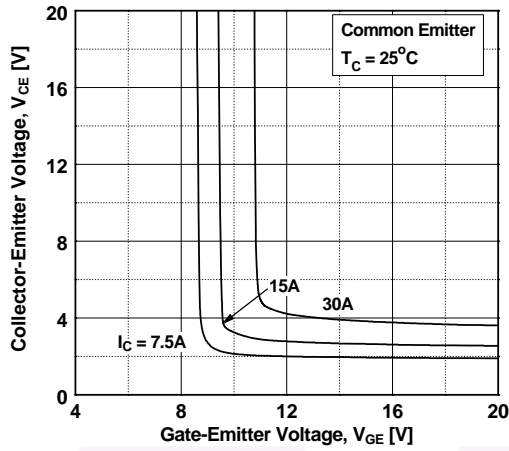


Figure 8. Capacitance Characteristics

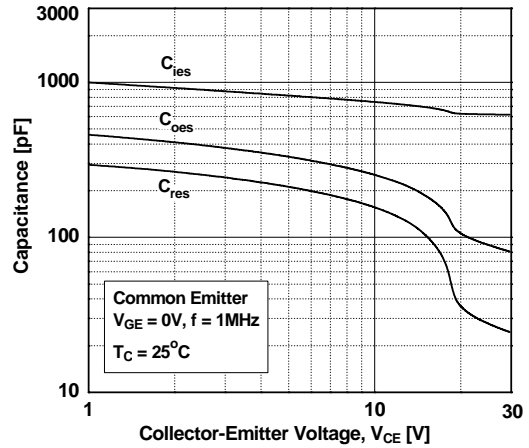


Figure 9. Gate charge Characteristics

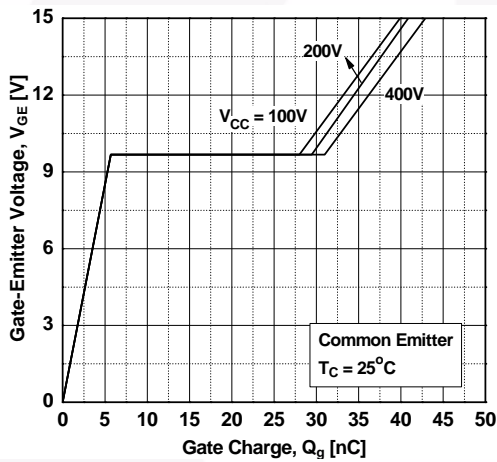


Figure 10. SOA Characteristics

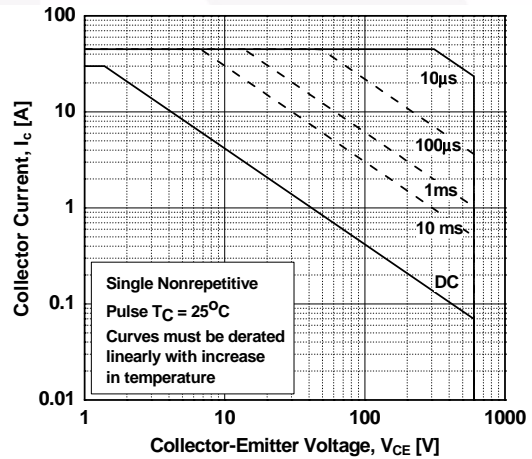


Figure 11. Turn-on Characteristics vs. Gate Resistance

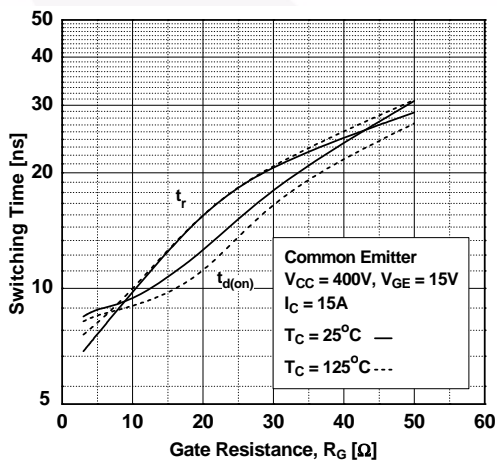
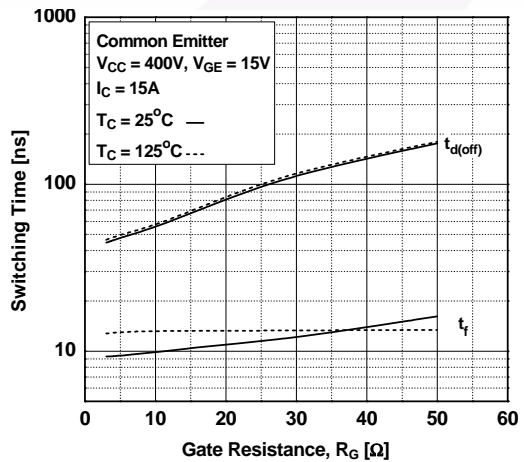
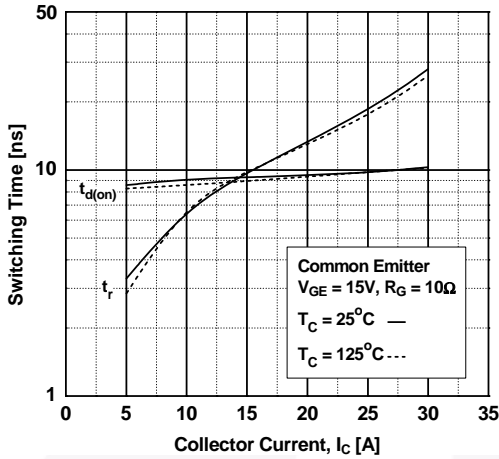


Figure 12. Turn-off Characteristics vs. Gate Resistance

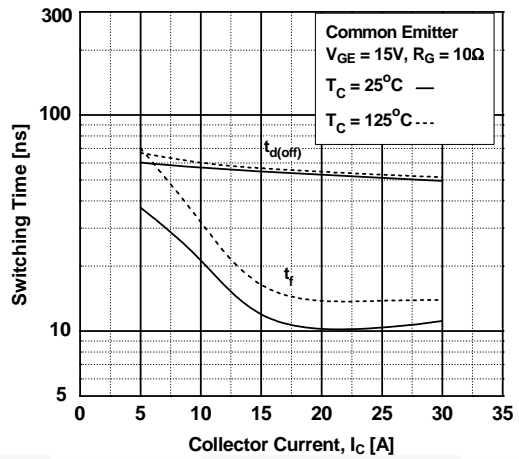


## Typical Performance Characteristics

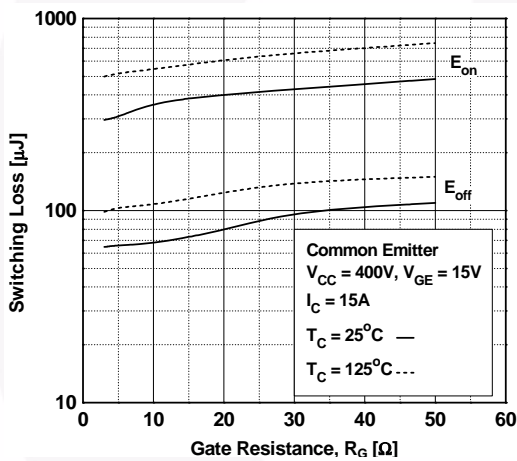
**Figure 13. Turn-on Characteristics vs. Collector Current**



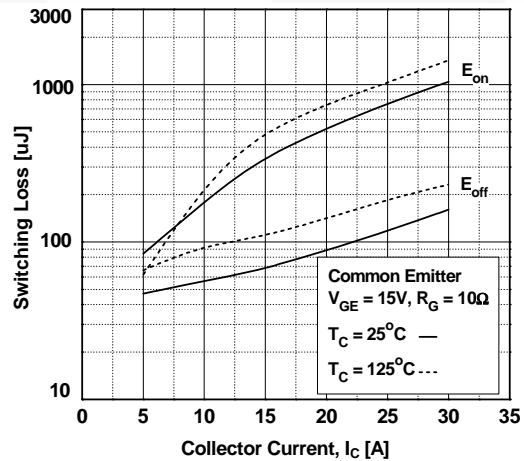
**Figure 14. Turn-off Characteristics vs. Collector Current**



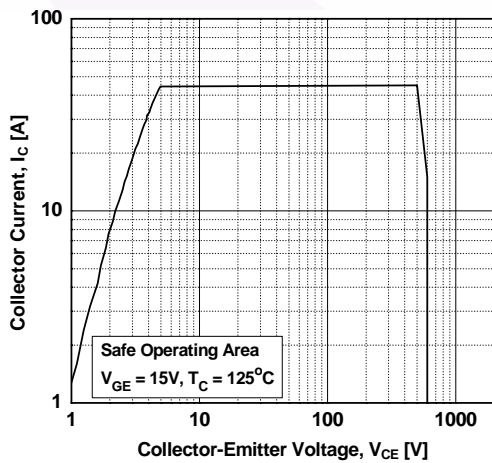
**Figure 15. Switching Loss vs. Gate Resistance**



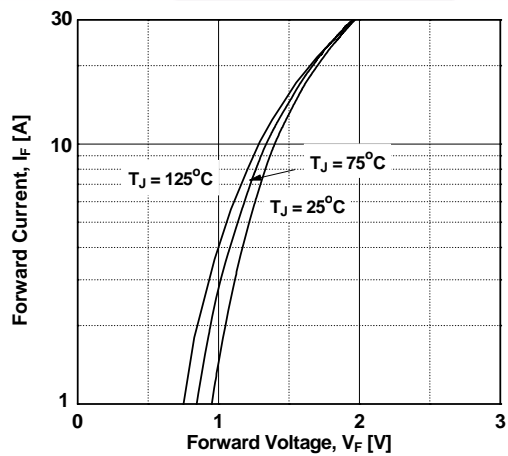
**Figure 16. Switching Loss vs. Collector Current**



**Figure 17. Turn off Switching SOA Characteristics**



**Figure 18. Forward Characteristics**



## Typical Performance Characteristics

Figure 19. Reverse Current

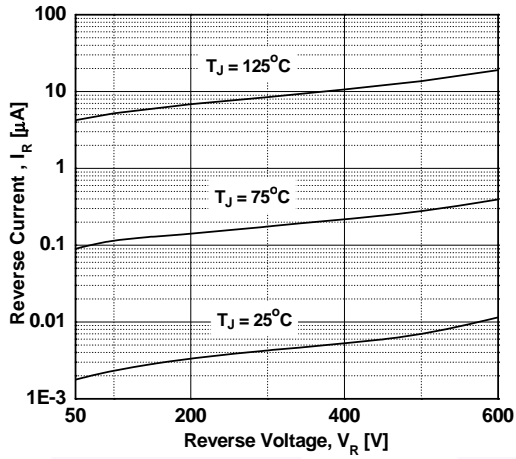


Figure 20. Stored Charge

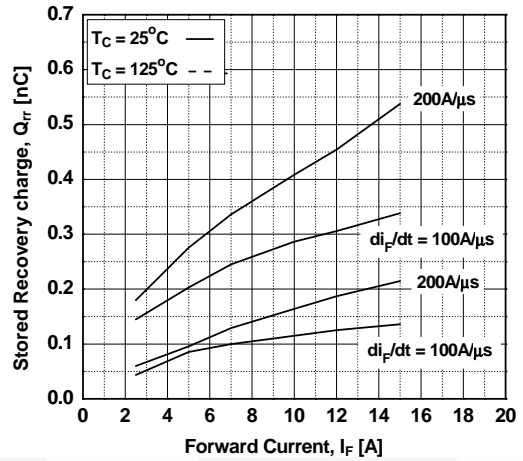


Figure 21. Reverse Recovery Time

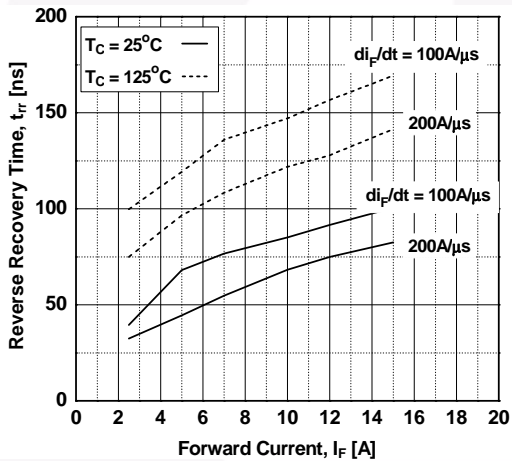
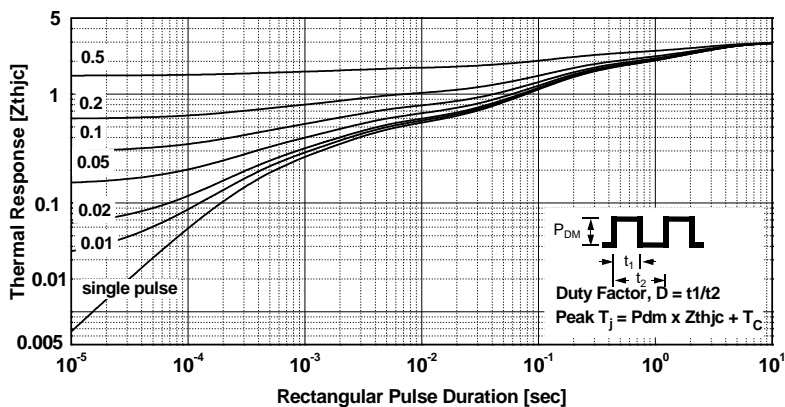
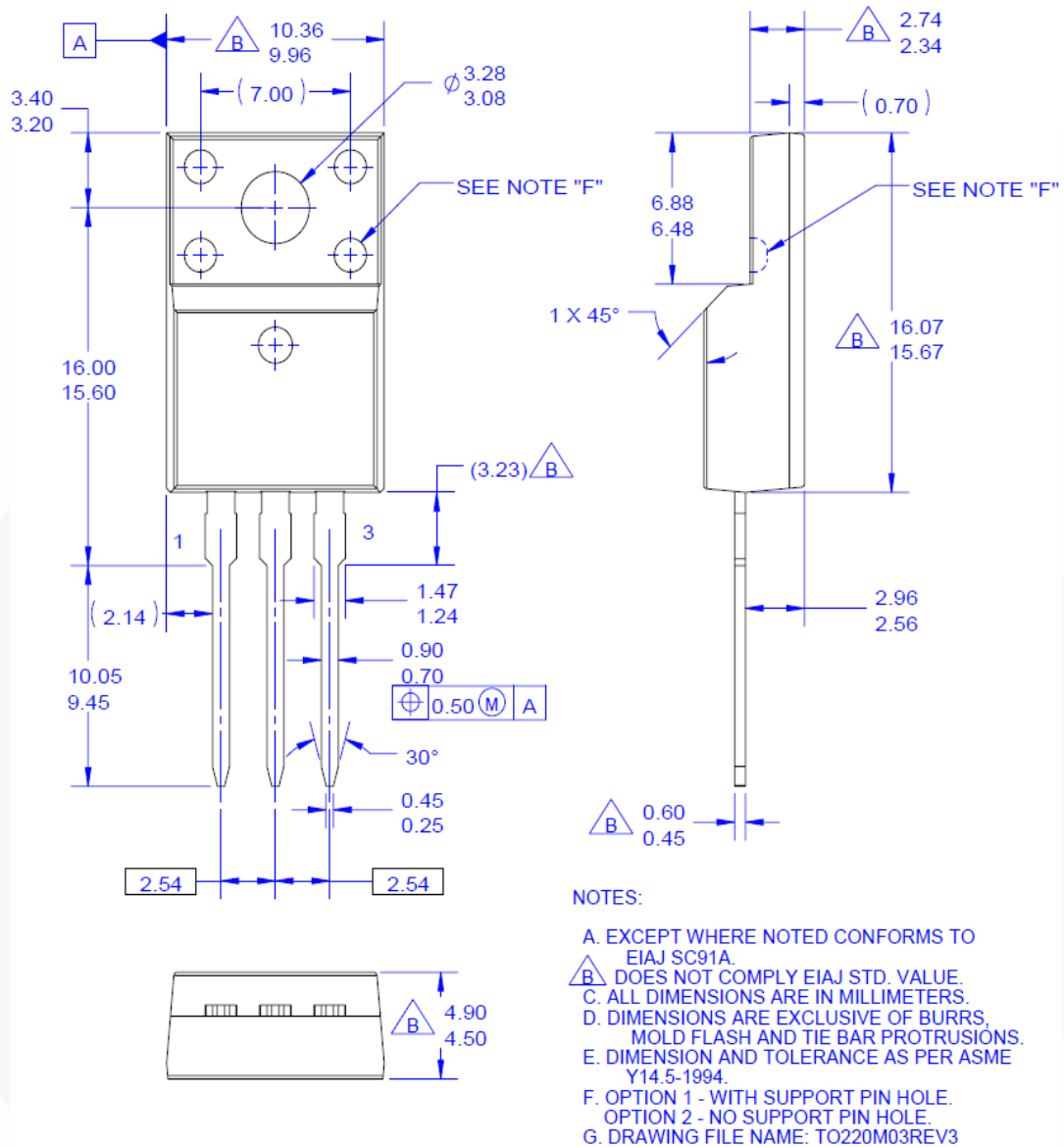


Figure 22. Transient Thermal Impedance of IGBT



## Mechanical Dimensions



**Figure 23. TO-220F 3L - TO220, MOLDED, 3LD, FULL PACK, EIAJ SC91, STRAIGHT LEAD**

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Dimensions in Millimeters





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- |  |   |   |  |
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| AX-CAP®*   | FRFET®  | PowerXS™  |  SYSTEM®* |
| BitSiC™  | Global Power Resource <sup>SM</sup>             | Programmable Active Droop™  | TinyBoost®   |
| Build it Now™  | GreenBridge™                                    | QFET®   | TinyBuck™  |
| CorePLUS™  | Green FPS™                                      | QS™   | TinyCalc™  |
| CorePOWER™   | Green FPS™ e-Series™                            | Quiet Series™   | TinyLogic®   |
| CROSSVOLT™   | Gmax™   | RapidConfigure™   | TINYOPTO™  |
| CTL™   | GTO™  |  Saving our world, 1mW/W/kW at a time™ | TinyPower™   |
| Current Transfer Logic™  | IntelliMAX™                                     | SignalWise™   | TinyPWM™   |
| DEUXPEED®  | ISOPLANAR™                                      | SmartMax™   | TinyWire™  |
| Dual Cool™   | Marking Small Speakers Sound Louder and Better™ | SMART START™  | TranSiC™   |
| EcoSPARK®  | MegaBuck™                                       | Solutions for Your Success™   | TriFault Detect™   |
| EfficientMax™  | MICROCOUPLER™                                   | SPM®  | TRUECURRENT®*  |
| ESBC™  | MicroFET™                                       | STEALTH™  | µSerDes™   |
|  Fairchild® | MicroPak™                                       | SuperFET®   |  SerDes®  |
| Fairchild Semiconductor®   | MicroPak2™                                      | SuperSOT™-3   | UHC®   |
| FACT Quiet Series™   | MillerDrive™                                    | SuperSOT™-6   | Ultra FRFET™   |
| FACT®  | MotionMax™                                      | SuperSOT™-8   | UniFET™  |
| FAST®  | mWSaver®  | SupreMOS®   | VCX™   |
| FastvCore™   | OptoHiT™  | SyncFET™  | VisualMax™   |
| FETBench™  | OPTOLOGIC®                                      |   | VoltagePlus™   |
| FPS™   | OPTOPLANAR®                                     |   | XS™  |

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Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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